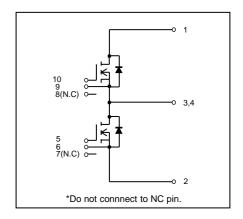
Application

- · Motor drive
- · Inverter, Converter
- · Photovoltaics, wind power generation.
- · Induction heating equipment.

Features

- 1) Low surge, low switching loss.
- 2) High-speed switching possible.
- 3) Reduced temperature dependence.

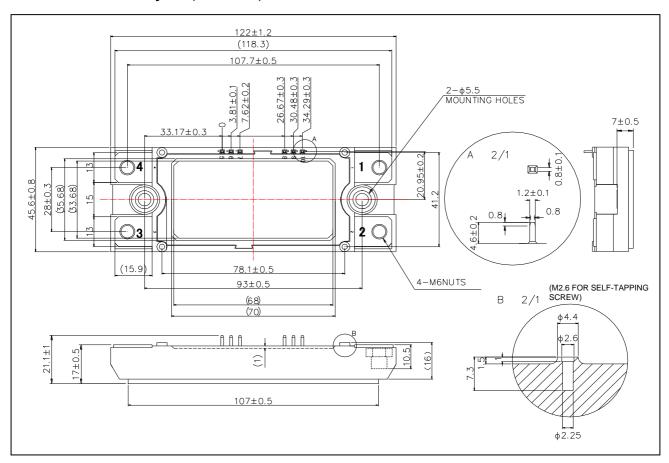
●Circuit diagram



Construction

This product is a half bridge module consisting of SiC-DMOS from ROHM.

● Dimensions & Pin layout (Unit : mm)



● Absolute maximum ratings (Tj = 25°C)

Parameter	Symbol	Conditions	Limit	Unit
Drain-source voltage	V_{DSS}	G-S short	1200	V
Gate-source voltage(+)	V_{GSS}	D-S short	22	V
Gate-source voltage(-)	V GSS	D-3 SHOIL	-6	V
Drain current *1	I_D	DC(Tc=60°C)	180	Α
	I _{DRM}	Pulse (Tc=60°C) 1ms *2	360	Α
Source current *1	I _S	Tc=60°C	180	Α
	I _{SRM} *2*3	Pulse (Tc=60°C) 1ms V _{GS} =18V	360	Α
		Pulse (Tc=60°C) 10μs V _{GS} =0V	360	Α
Total power disspation *4	Ptot	Tc=25°C	1130	W
Junction temperature	Tj		-40 to150	°C
Storage temperature	Tstg		-40 to125	°C
Isolation voltage*5	Visol	Terminals to baseplate, f=60Hz AC 1min.	2500	Vrms
Mounting torque		Main Terminals : M6 screw	4.5	N · m
	_	Mounting to heat shink: M5 screw	3.5	N·m

^(*1) Measurement of Tc is to be done at the point just under the chip.

●Electrical characteristics (Tj=25°C)

Parameter	Symbol	Conditions		Min.	Тур.	Max.	Unit
Static drain-source on-state	V	I _C =180A, V _{GS} =18V	Tj=25°C	-	2.3	3.2	V
voltage	V _{DS(on)}	1C-100A, V _{GS} -10V	Tj=125°C	ı	3.3	4.4	V
Drain cutoff current	I _{DSS}	V _{DS} =1200V, V _{GS} =0V		ı	-	10	μΑ
Source-drain voltage	V	V _{GS} =0V, I _S =180A	Tj=25°C	-	5.4	-	V
			Tj=125°C	-	5.1	-	
	V_{SD}	V _{GS} =18V, I _S =180A	Tj=25°C	-	2.3	-	
			Tj=125°C	-	3.3	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =10V, I _D =35.2mA		1.6	2.7	4.0	V
Gate-source leakage current	_	V _{GS} =22V, V _{DS} =0V		-	-	0.5	μΑ
	I_{GSS}	$V_{GS} = -6V, V_{DS} = 0V$		-0.5	-	-	μΑ
Switching characteristics	td(on)	V _{GS(on)} =18V, V _{GS(off)} =0V		-	80	-	ns
	tr	V _{DS} =600V I _D =180A		-	90	-	ns
	trr			1	50	-	ns
	td(off)	$R_G=5.6\Omega$		-	300	-	ns
	tr	inductive load		-	90	-	ns
Input capacitance	Ciss	V _{DS} =10V, V _{GS} =0V, f=1MHz		1	23	-	nF
Internal gate resistor	R_{Gint}	Tj=25°C		-	1.15	-	Ω
Junction-to-case thermal resistance		DMOS (1/2 module) *6		-	-	0.11	°C/W
Case-to-heat sink Thermal resistance	Rth(c-f)	Case to heat sink, per 1 module, Thermal grease appied *7		-	0.035	-	°C/W

^(*6) Measurement of Tc is to be done at the point just beneath the chip.

^(*2) Repetition rate should be kept within the range where temperature rise of die should not exceed Tj max.

^(*3) Duration of current conduction at gate-off state should not exceed 10µsec.

^(*4) Tj is less than 150°C (*5) Actual measurement is 3000Vrms/1sec. in accordance with UL1557.

^(*7) Typical value is measured by using thermally conductive grease of λ =0.9W / (m · K).

Waveform for switching test

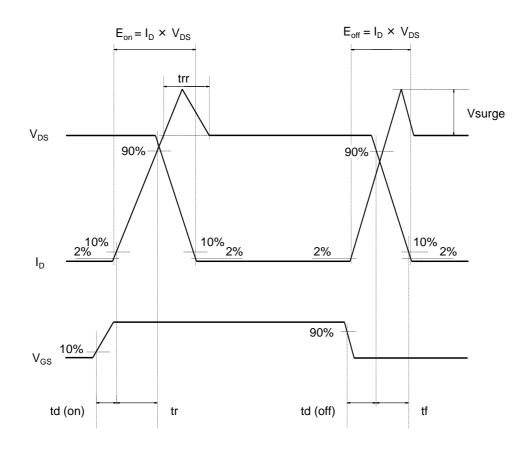
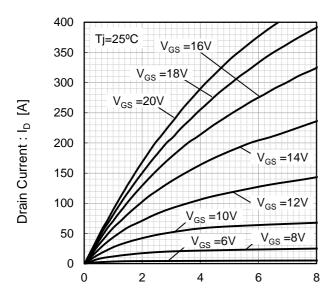
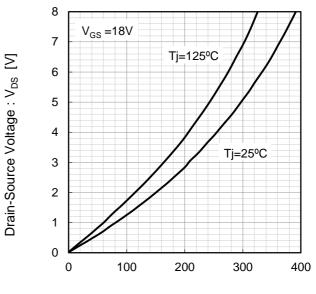


Fig.1 Typical Output Characteristics



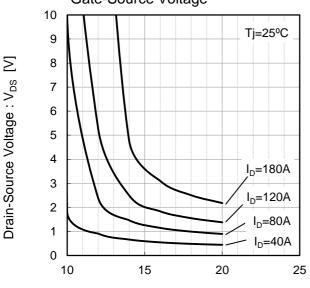
Drain-Source Voltage: V_{DS} [V]

Fig.2 Drain-Source Voltage vs. Drain Current



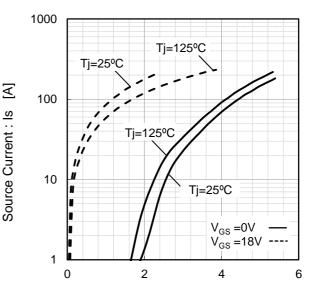
Drain Current : I_D [A]

Fig.3 Drain-Source Voltage vs. Gate-Source Voltage



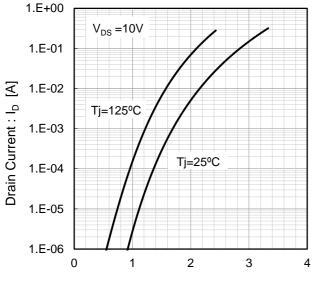
Gate-Source Voltage : V_{GS} [V]

Fig.4 Forward characteristic of Diode



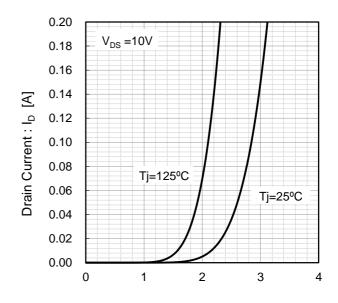
Source-Drain Voltage: V_{SD} [V]

Fig.5 Drain Current vs. Gate-Source Voltage



Gate-Source Voltage : V_{GS} [V]

Fig.6 Drain Current vs. Gate-Source Voltage



Gate-Source Voltage : V_{GS} [V]

Fig.7 Switching Characteristics [Tj=25°C]

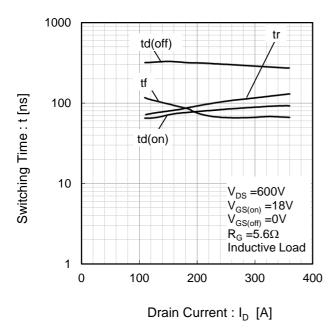
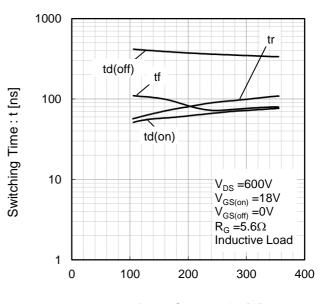
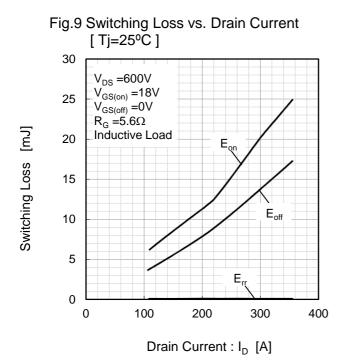
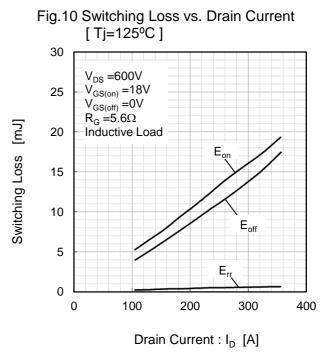


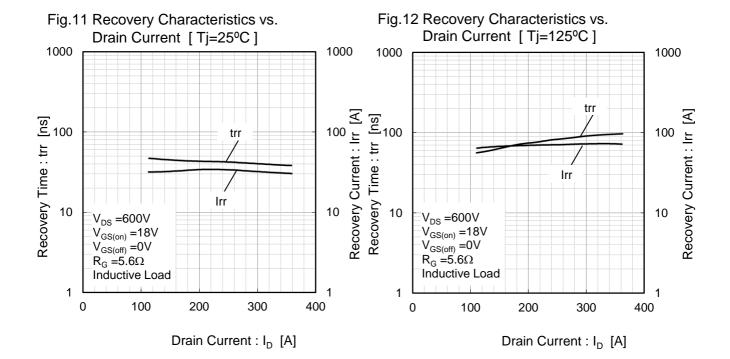
Fig.8 Switching Characteristics [Tj=125°C]



Drain Current : I_D [A]







Gate Resistance : R_G [Ω]

Fig.14 Switching Characteristics vs. Gate Resistance [Tj=125°C] $V_{DS} = 600V$ $V_{DS} = 180A$ $V_{GS(on)} = 18V$ $V_{GS(off)} = 0V$ Inductive Load 100 10 1 $Gate Resistance : R_G [\Omega]$

Fig.15 Switching Loss vs. Gate Resistance [Tj=25°C] 20 18 16 14 Switching Loss [mJ] 12 $\mathsf{E}_{\mathsf{off}}$ 10 8 $V_{DS} = 600V$ $I_{D} = 180A$ 6 4 $V_{GS(on)} = 18V$ $V_{GS(off)} = 0V$ 2 Inductive Load E_{rr} 0 10 100 1 Gate Resistance : R_G [Ω]

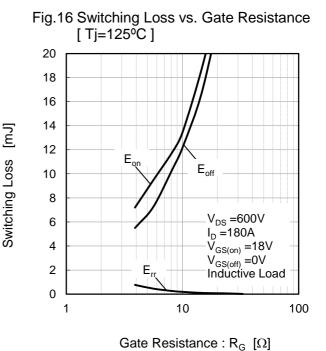




Fig.17 Typical Capacitance vs. Drain-Source Voltage

1.E-07

1.E-08

1.E-09

1.E-10 $T_{j=25^{\circ}C}$ $V_{gs}=0V$ 1.E-11

1.001

1 100

Drain-Source Voltage: V_{DS} [V]

Fig.18 Gate Charge Characteristics [$Tj=25^{\circ}C$]

25 $I_{D}=180A$ $Tj=25^{\circ}C$ 20

15

0

5

0

5

0

1000

1500

Total Gate charge: Qg [nC]

Fig.19 Normalized Transient Thermal Impedance

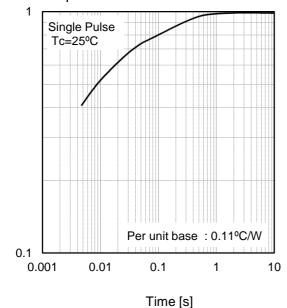
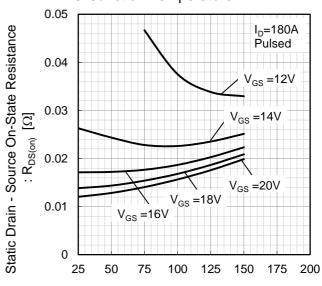


Fig.20 Static Drain - Source On-State Resistance vs. Junction Temperature



Junction Temperature : Tj [°C]

Normalized Transient Thermal Impedance: Rth

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